however, is an exception. It concentrates on the solid-state version and supplies both the theoretical background of the physical principles the devices are based on and a disclosure of practical possibilities and limitations.

After a brief introduction to maser theory and some magnetic relations in a medium, the author starts with a quantum-mechanical description of the internal structure and the magnetic properties of atoms. He then concentrates on paramagnetic maser materials. Chapter 5 is a well-written survey of paramagnetic resonance using both the relaxation of the spinlattice system and Bloch's approach (dynamic behavior of macroscopic magnetization in a nuclear paramagnetic material). In the next chapter Bloembergen's three-level solid-state maser is dealt with, both as an amplifier and as an oscillator. The author also considers briefly the problem of harmonic pumping. Further on he discusses the traveling-wave maser, considering first the amplification mechanism and then passing on to bandwidth and tuning considerations and to properties of the interaction structure. This section also has a concise discussion of traveling-wave tube problems. In Chapter 8 noise generation in maser spin systems is considered, and here the author uses the well-suited wave approach. sources of these perturbations and their measurement are dealt with, and some discussion is added on the quantum aspect of amplification and noise. The last chapter considers a number of practical maser devices, their performance figures and important experimental techniques involved. A very useful table of properties and suppliers of maser materials is included. In an appendix the ruby energy level and transition-probability matrix elements are given. An index and a bibliography containing about 350 references on solid-state maser problems and about 280 references on paramagnetic resonance and relevant topics are attached.

Siegman's book is an excellent handbook on microwave solid-state masers, both as a detailed and concise introduction leading the student and research worker to a very high level of understanding and as a reference book for the scientist working in the field. It is quite certain that this book will very soon belong to every library, private or public, containing books on masers and paramagnetic resonance. It may be highly recommended to every scientist in the field and to people having both a deep interest in maser problems and a good physical knowledge. The book is worth the price and will not be out-dated for quite a long time.

The Chemistry of Imperfect Crystals. By F. A. Kröger. 1039 pp. North-Holland, Amsterdam, 1964. \$30.80.
Reviewed by Norman H. Nachtrieb, University of Chicago.

This book is significant as a comprehensive treatment of the defect crystalline state, insofar as imperfections are responsible for the chemical behavior of solids. Its author is a staff member of the Philips' Research Laboratories in Eindhoven, Holland, long distinguished for contributions to the research literature on the luminescence of solids.

Crystalline solids would be chemically uninteresting substances were it not for the imperfections they possess. Even the most superficial tarnishing reaction would not proceed much beyond the depth of a single lattice spacing in their absence. Broadly speaking, imperfections fall into one of two categories: lattice defects and electronic defects. Much has been learned during the past two decades about their properties, and techniques have been devised to regulate and control them for useful purposes. Kröger's monograph is an effort to summarize most of what is important in the thermodynamic and kinetic behavior of crystal imperfections. On the whole, this has been accomplished in a very successful manner. It is highly readable, up to date, and critical.

The first of its twenty-five chapters is devoted to the principles of purification of materials, the growth of single crystals, and doping. Succeeding chapters are concerned with the thermodynamics of phase diagrams and a survey of the laws of dilute solutions, with particular reference to solid solutions. The detailed dis-

cussion of lattice imperfections (vacancies and interstitial atoms) of electronic defects (electrons and holes) is particularly well done. The simple law of mass action and the principle of electroneutrality suffice for the description of most of the chemical equilibria encountered at low-defect concentrations. Imperfections may interact with one another, of course, forming ion pairs and higher associates when they are charged, and requiring a Debye-Hückel kind of correction when their concentration becomes appreciable. They may also interact with impurity atoms and modify solubility relations, or alter the stoichiometry of the host substance. Kröger carefully points out that although electronic defects are usually in equilibrium with a crystal, it is often the case that lattice imperfections are not: the thermal history and ambient gas composition during the growth and annealing of crystals are often dominant factors in the reactivities of solids. In a systematic manner, separate chapters deal with imperfection equilibria in pure elemental substances, and with the effects of one and two kinds of foreign atoms on these equilibria. Similar considerations are then given to compounds (oxides, sulfides, alkali halides, and to such complex systems as spinels, perovskites, and ice). Relaxation effects in solids, including the kinetics of clustering and precipitation reactions, the diffusion of color centers, and the migration of charged imperfections are considered in one chapter.

The last five chapters represent the application of the principles of crystaldefect chemistry to particular problems, notably sintering, tarnishing reactions, solid-state batteries, fuel cells, electrolytic capacitors, and the photographic process. Particularly interesting, although admittedly still speculative, is a discussion of the heterogeneous catalysis of charge-transfer gas reactions by semiconductor surfaces. The over-all process involves adsorption, surface reaction, and desorption when donor and acceptor molecules combine with one another to form a product molecule. The slow step is presumed to be the chargetransfer reaction, in which ionized

# Berkeley Physics Course and Laboratory

A fresh and modern approach to the teaching of experimental physics at the introductory level 

This is a two-year college physics program for students majoring in science and engineering. The purpose of the program is to present the elementary ideas of physics in a spirit that well represents their role in current research in the field. The course and laboratory are designed to reflect vigorously the revolutions in physics in the last hundred years. The project was developed by an inter-university group centered at the University of California at Berkeley consisting of 

Eugene D. Commins, Frank S. Crawford, Jr., Charles Kittel, Walter D. Knight, Philip Morrison, Alan M. Portis, Edward M. Purcell, Frederick Reif, Malvin A. Ruderman, and Eyvind H. Wichmann.

Now available 

Laboratory Physics Part A by the Berkeley Physics Laboratory 

Designed for the first semester of introductory physics for science and engineering students 

Developed by Professor Alan M. Portis 

A detailed description of the Berkeley Physics Laboratory appears in the June issue of the American

#### Experiments in Part A

1. Acceleration and deflection of electronics

Journal of Physics, Volume 32, Number 6, pages 458-64.

- 2. Magnetic deflection of electrons
- 3. Helical motion of electrons
- 4. Time of flight of electrons
- 5. Exponential relaxation
- 6. Damped oscillations
- 7. Frequency response
- 8. Resonance
- 9. Nonlinearity
- 10. Modulation
- 11. Negative resistance
- 12. Relaxation oscillations

Parts B and C to follow. Examination copies of Part A available on request.

Forthcoming: The Projected Five Volumes of 

The Berkeley Physics Course

Volume I: Mechanics

Volume II: Electricity and Magnetism Volume III: Waves and Oscillations

Volume IV: Quantum Physics Volume V: Statistical Physics

McGraw-Hill Book Company ☐ 330 West 42nd Street ☐ New York, New York 10036

### SPRINGER-VERLAG NEW YORK INC.

# Neutron Physics

by K. H. Beckurts and K. Wirtz

Translated from the German by L. Dresner, Oak Ridge National Laboratory

#### Contents:

Revised edition. 293 illustrations, 454 pp. 8vo. 1964. Cloth \$17

Production and nuclear interaction of neutrons.

The theory of neutron fields.

The determination of flux and spectrum in a neutron field.

The determination of neutron transport parameters.

#### SPRINGER-VERLAG NEW YORK INC.

175 Fifth Avenue New York/N.Y. 10010

Please send me	copies of ?	NEUTRON	PHYSICS, \$17
----------------	-------------	---------	---------------

- Please send me a leaflet and catalogs in this field
- Payment enclosed (Add sales tax where necessary)
- Charge my established account

\_\_Address\_\_

\_\_Zone \_\_\_\_\_ State \_\_\_\_\_ Zip No.\_\_\_

Or to your bookseller

## SCIENTISTS for semiconductor research

to work in the fields of...

Injection Lasers, Thin Film Active Devices, Microcircuitry Techniques, Microwave Devices.

Several unusual positions are now available for scientists with experience in semiconductor device technology at either the research or advanced development levels. Selected candidates must be capable of conducting independent research programs in the above areas.

The objectives of these programs encompass an understanding of the basic phenomena underlying device performance, as well as a demonstration of the feasibility of advanced device concepts.

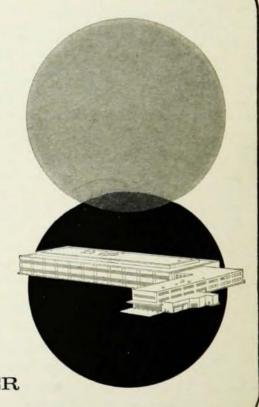
If you have a Ph.D. or M.S. in Physics, Physical Chemistry or Electrical Engineering with at least one year's experience in device studies, you are invited to write to the Research Center.

We offer a unique opportunity to qualified individuals to conduct research in a creative scientific environment which encourages the publication of results, in association with many prominent scientists.

For further information, please write Mr. Rodney C. Davis.

#### SPERRY RAND RESEARCH CENTER

Box 400, Sudbury, Massachusetts An equal opportunity employer



donor and acceptor molecules are formed on a reactive surface site.

Like most books, this one has its share of errors, but they are neither excessive nor particularly serious. Fick's second law for diffusion is mistakenly written with a negative sign several times on page 794. Equation (6.11), the relation between the sulfur and oxygen pressures which prevails when ZnS and ZnO are in equilibrium with each other, should read,  $p_{82}^{\frac{1}{2}}/p_{02}^{\frac{3}{2}}.$ 

Equation (9.10) is also in error, and should read,

In  $K_0 = (\Sigma_V \circ s^0/k) = (\Delta S^0/R)$ . More annoying than such errors, which are readily seen and discounted, are the many undersized figures that appear in the text. When all of this is said, it is nevertheless an excellent book. What a pity that its excessive cost will limit it to the libraries of the more affluent institutions!

Progress in Brain Research. Vol. 2. Nerve, Brain, and Memory Models. N. Wiener and J. P. Schadé, eds. 280 pp. Elsevier, New York, 1963. \$15.00.

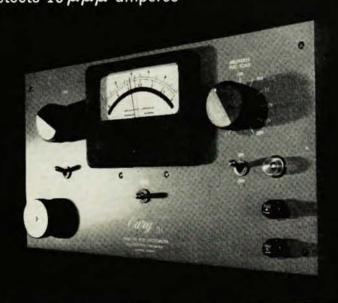
Reviewed by Joseph G. Hoffman, State University of New York at Buffalo.

Twenty papers on the operations of the nervous system have been contributed to this volume by twenty-five authors. Fifteen papers are in English, three in French, and two in German. They present original work on neurocybernetics which deals "with the pathways of action via senseorgans, neurons and effectors". As editor, Norbert Wiener wrote in the Introduction, "the nervous system is unbelievably complex", and this complexity requires the collaboration of neurologists, psychiatrists, biologists, engineers, mathematicians, and physicists for its elucidation. The integrated nervous system is a formidable object which has not yet been adequately described; new words have to be coined. To quote Wiener again: ". . . You cannot hope to get people of these different disciplines to produce cybernetic work merely because they are brought together. They must understand language, methods, and thoughts of the others."

All of the papers achieve high standards of presentation and are

## CARY MODEL 31 ELECTROMETER

senses 0.02 mv with  $10^7$  kilomegohm input impedance measures  $10^9$  megohms  $\pm 1\%$  at 1 volt detects  $10\,\mu\mu\mu$  amperes



For specifications and application details write for Data File P240-104

This vibrating reed electrometer offers versatility with amazing accuracy. Ideal for Hall effect, diode reverse current studies and other semiconductor measurements, the Model 31 is unequalled for testing dielectric resistance, charging and hysteresis phenomena, ionization and radiation levels. It finds wide application in measuring electrochemical, photoelectric, piezoelectric and thermoelectric properties of matter. • Sensitivity is  $10^{-17}$  amperes, 0.02 millivolts. • Drift less than  $5 \times 10^{-17}$  amperes, open circuit; less than 0.1 mv per day, shorted input. • Accuracy for absolute EMFs is  $\pm 0.25\%$ ,  $\pm 0.01$  mv using precision potentiometer and recorder,  $\pm 1\%$  using panel meter. • Input Impedance of  $10^{16}$  ohms prevents test circuit loading. Model 31 performance is free from effects of grid current and virtually independent of vacuum tube or component changes.

APPLIED PHYSICS CORPORATION 2724 SOUTH PECK ROAD MONROVIA, CALIFORNIA

INSTRUMENTS

Raman/UV/IR Recording Spectrophotometers • Vibrating Reed Electrometers